

TRENCHSTOP™ 5 Advanced Isolation

Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	650	V
DC collector current, limited by T_{vjmax} $T_h = 25^{\circ}\text{C}$ value limited by bondwire $T_h = 65^{\circ}\text{C}$ $T_h = 65^{\circ}\text{C}$	I_C	80.0 66.0 104.0 ¹⁾	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	240.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$	-	240.0	A
Diode forward current, limited by T_{vjmax} $T_h = 25^{\circ}\text{C}$ value limited by bondwire $T_h = 65^{\circ}\text{C}$	I_F	80.0 74.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	240.0	A
Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$)	V_{GE}	± 20 ± 30	V
Power dissipation $T_h = 25^{\circ}\text{C}$ Power dissipation $T_h = 65^{\circ}\text{C}$	P_{tot}	148.0 109.0	W
Operating junction temperature	T_{vj}	-40...+175	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55...+150	$^{\circ}\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm
Isolation voltage RMS, $f = 50/60\text{Hz}$, $t = 1\text{min}^{2)}$	V_{isol}	2500	V

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R_{th} Characteristics						
IGBT thermal resistance, ³⁾ junction - heatsink	$R_{th(j-h)}$		-	0.86	1.01	K/W
Diode thermal resistance, ³⁾ junction - heatsink	$R_{th(j-h)}$		-	0.97	1.14	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		-	-	65	K/W

¹⁾ Equivalent current rating in TO-247-3 at $T_h = 65^{\circ}\text{C}$ using reference insulation material: 152 μm , 0.9 W/mK, standard polyimide based reinforced carrier insulator

²⁾ For a proper handling and assembly of the advanced isolation device in the application refer to the note at the package drawing.

³⁾ At force on body $F = 500\text{N}$, $T_a = 25^{\circ}\text{C}$

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Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}, I_C = 0.50\text{mA}$	650	-	-	V
Collector-emitter saturation voltage	V_{CESat}	$V_{GE} = 15.0\text{V}, I_C = 60.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	1.65 1.95	2.10 -	V
Diode forward voltage	V_F	$V_{GE} = 0\text{V}, I_F = 60.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	1.45 1.39	1.70 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.60\text{mA}, V_{CE} = V_{GE}$	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	- -	40 2000	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20\text{V}, I_C = 60.0\text{A}$	-	72.0	-	S

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$ $f = 1000\text{kHz}$	-	3600	-	pF
Output capacitance	C_{oes}		-	105	-	
Reverse transfer capacitance	C_{res}		-	13	-	
Gate charge	Q_G	$V_{CC} = 520\text{V}, I_C = 60.0\text{A},$ $V_{GE} = 15\text{V}$	-	144.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 60.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega,$ $L_{\sigma} = 30\text{nH}, C_{\sigma} = 30\text{pF}$ L_{σ}, C_{σ} from Fig. E Energy losses include "tail" and diode reverse recovery.	-	30	-	ns
Rise time	t_r		-	35	-	ns
Turn-off delay time	$t_{d(off)}$		-	206	-	ns
Fall time	t_f		-	42	-	ns
Turn-on energy	E_{on}		-	1.80	-	mJ
Turn-off energy	E_{off}		-	0.60	-	mJ
Total switching energy	E_{ts}		-	2.40	-	mJ